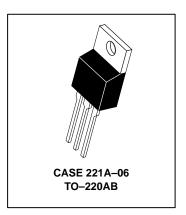
# **Complementary Silicon Power Transistors**

These complementary silicon power transistors are designed for high–speed switching applications, such as switching regulators and high frequency inverters. The devices are also well–suited for drivers for high power switching circuits.

- Fast Switching tf = 90 ns (Max)
- Key Parameters Specified @ 100°C
- Low Collector–Emitter Saturation Voltage VCE(sat) = 1.0 V (Max) @ 8.0 A
- Complementary Pairs Simplify Circuit Designs



15 AMPERE
COMPLEMENTARY
SILICON
POWER TRANSISTORS
80 VOLTS
83 WATTS



# **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	80	Vdc
Collector–Emitter Voltage	V <sub>CEV</sub>	100	Vdc
Emitter Base Voltage	V <sub>EB</sub>	7.0	Vdc
Collector Current — Continuous — Peak (1)	I <sub>C</sub>	15 20	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	83 0.67	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.5	°C/W
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	62.5	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	$T_L$	275	°C

(1) Pulse Width  $\leq$  6.0 ms, Duty Cycle  $\leq$  50%.

NOTE: All polarities are shown for NPN transistors. For PNP transistors, reverse polarities.



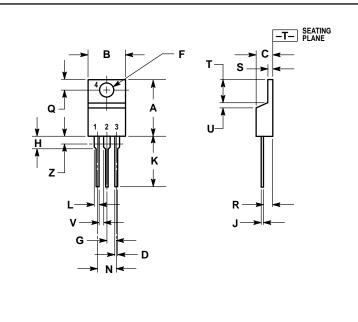
## D44VH D45VH

# **ELECTRICAL CHARACTERISTICS** (T $_{C}$ = 25 $^{\circ}$ C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•		
Collector–Emitter Sustaining Voltage (1) (I <sub>C</sub> = 25 mAdc, I <sub>B</sub> = 0)		VCEO(sus)	80	_	_	Vdc
Collector–Emitter Cutoff Current  (VCE = Rated VCEV, VBE(off) = 4.0 Vdc)  (VCE = Rated VCEV, VBE(off) = 4.0 Vdc, TC = 100°C)		ICEV	_		10 100	μAdc
Emitter Base Cutoff Current (V <sub>EB</sub> = 7.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	_	_	10	μAdc
ON CHARACTERISTICS (1)						
DC Current Gain (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 1.0 Vdc) (I <sub>C</sub> = 4.0 Adc, V <sub>CE</sub> = 1.0 Vdc)		hFE	35 20	_	_ _	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc) (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc) (I <sub>C</sub> = 15 Adc, I <sub>B</sub> = 3.0 Adc, T <sub>C</sub> = 100 $^{\circ}$ C)	D44VH10 D45VH10 D44VH10 D45VH10	VCE(sat)	_ _ _ _		0.4 1.0 0.8 1.5	Vdc
Base–Emitter Saturation Voltage  (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc)  (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc)  (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.4 Adc, T <sub>C</sub> = 100°C)  (I <sub>C</sub> = 8.0 Adc, I <sub>B</sub> = 0.8 Adc, T <sub>C</sub> = 100°C)	D44VH10 D45VH10 D44VH10 D45VH10	V <sub>BE</sub> (sat)	_ _ _ _		1.2 1.0 1.1 1.5	Vdc
DYNAMIC CHARACTERISTICS						
Current Gain Bandwidth Product (I <sub>C</sub> = 0.1 Adc, V <sub>CE</sub> = 10 Vdc, f = 20 MHz)		fΤ	_	50	_	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>C</sub> = 0, f <sub>test</sub> = 1.0 MHz)	D44VH10 D45VH10	C <sub>ob</sub>	_	120 275	_ _	pF
SWITCHING CHARACTERISTICS						
Delay Time		<sup>t</sup> d	_	_	50	ns
Rise Time (V <sub>CC</sub> = 20 Vdc, I <sub>C</sub> = 8.0 dc,	$(V_{CC} = 20 \text{ Vdc}, I_{C} = 8.0 \text{ Adc},$		_	_	250	
Storage Time I <sub>B1</sub> = I <sub>B2</sub> = 0.8 Adc)		t <sub>S</sub>	_	_	700	
Fall Time		t <sub>f</sub>			90	

<sup>(1)</sup> Pulse Test: Pulse Width  $\leq 300 \,\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

# **PACKAGE DIMENSIONS**



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.570	0.620	14.48	15.75
В	0.380	0.405	9.66	10.28
С	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.42	2.66
Н	0.110	0.155	2.80	3.93
J	0.018	0.025	0.46	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
Т	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
٧	0.045		1.15	
Z		0.080		2.04

STYLE 1:
PIN 1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

**CASE 221A-06** TO-220AB **ISSUE Y** 

#### D44VH D45VH

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How to reach us:

**USA/EUROPE**: Motorola Literature Distribution; P.O. Box 20912; Phoenix, Arizona 85036. 1–800–441–2447

MFAX: RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244–6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3–14–2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03–3521–8315

**HONG KONG:** Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852–26629298



